Abstracts

Microwave noise parameters of pseudomorphic GaInAs HEMTs under optical illumination

L. Escotte, K. Grenier, J.G. Tartarin and J. Graffeuil. "Microwave noise parameters of pseudomorphic GaInAs HEMTs under optical illumination." 1998 Transactions on Microwave Theory and Techniques 46.11 (Nov. 1998, Part I [T-MTT]): 1788-1789.

The microwave behavior of pseudomorphic high electron-mobility transistors (pHEMTs) under optical illumination is investigated in this paper. The influence of light on the small-signal equivalent circuit is derived from scattering-parameter measurements. The evolution of the noise parameters versus gate-to-source voltage and their sensibility to illumination is also demonstrated.

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